

Radar Pulsed Power Transistor 20W, 3.1-3.5 GHz, 100µs Pulse, 10% Duty

M/A-COM Products Released, 10 Aug 07

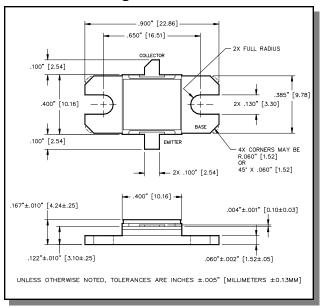
Features

- NPN silicon microwave power transistors
- Common base configuration
- Broadband Class C operation
- High efficiency inter-digitized geometry
- Diffused emitter ballasting resistors
- Gold metallization system
- Internal input and output impedance matching
- Hermetic metal/ceramic package
- · RoHS compliant

Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V _{CES}	65	V
Emitter-Base Voltage	V_{EBO}	3.0	V
Collector Current (Peak)	Ic	2.4	Α
Power Dissipation @ +25°C	P _{TOT}	200	W
Storage Temperature	T_{STG}	-65 to +200	°C
Junction Temperature	T_J	200	°C

Outline Drawing



Electrical Specifications: T_C = 25 ± 5°C (Room Ambient)

Parameter	Test Conditions	Frequency	Symbol	Min	Max	Units
Collector-Emitter Breakdown Voltage	I _C = 10mA		BV _{CES}	65	-	V
Collector-Emitter Leakage Current	V _{CE} = 40V		I _{CES}	-	1.5	mA
Thermal Resistance	Vcc = 36V, Pout = 20W	F = 3.1, 3.3, 3.5 GHz	R _{TH(JC)}	-	1.1	°C/W
Output Power	Vcc = 36V, Pout = 20W	F = 3.1, 3.3, 3.5 GHz	P _{IN}	-	3.6	W
Power Gain	Vcc = 36V, Pout = 20W	F = 3.1, 3.3, 3.5 GHz	G₽	7.5	=	dB
Collector Efficiency	Vcc = 36V, Pout = 20W	F = 3.1, 3.3, 3.5 GHz	ης	35	-	%
Input Return Loss	Vcc = 36V, Pout = 20W	F = 3.1, 3.3, 3.5 GHz	RL	-	-6	dB
Load Mismatch Tolerance	Vcc = 36V, Pout = 20W	F = 3.1, 3.3, 3.5 GHz	VSWR-T	-	2:1	-

Commitment to produce in volume is not qua

- North America Tel: 800.366.2266 / Fax: 978.366.2266
- Europe Tel: 44.1908.574.200 / Fax: 44.1908.574.300
- Asia/Pacific Tel: 81.44.844.8296 / Fax: 81.44.844.8298
 Visit www.macomtech.com for additional data sheets and product information.

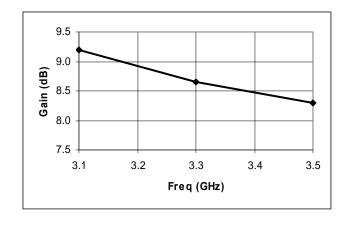


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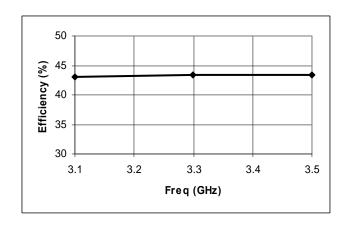
Typical RF Performance

Freq. (GHz)	Pin (W)	Pout (W)	Gain (dB)	Ic (A)	Eff (%)	RL (dB)	VSWR-T (2:1)
3.1	2.4	20	9.19	1.29	43.1	-10.2	Р
3.3	2.7	20	8.65	1.28	43.4	-10.9	Р
3.5	3.0	20	8.30	1.28	43.4	-13.0	Р

Gain vs. Frequency



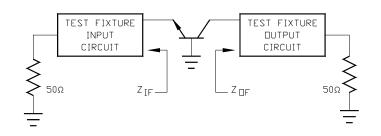
Collector Efficiency vs. Frequency



RF Test Fixture Impedance

typical. Mechanical outline has been fixed. Engineering samples Commitment to produce in volume is not guaranteed.

F (GHz)	Z _{IF} (Ω)	$Z_{OF}(\Omega)$
3.1	16.0 + j5.5	19.0 + j3.4
3.3	14.5 + j1.6	14.2 - j2.8
3.5	11.3 + j0.0	10.7 - j3.3



Solutions has under development. Performance is based on engineering tests. Specifications are

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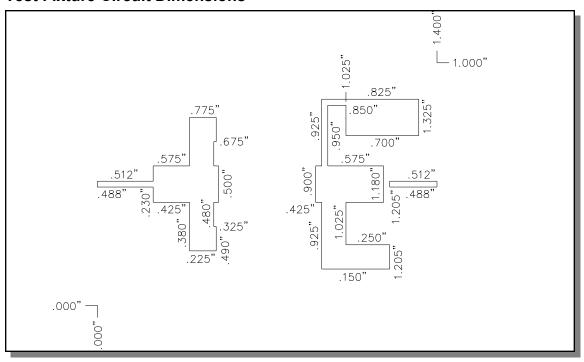
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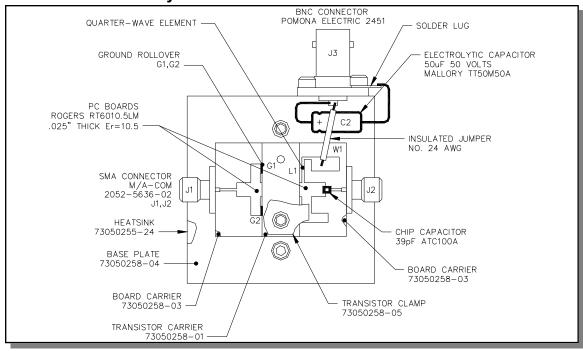
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Test Fixture Circuit Dimensions



Test Fixture Assembly



PRELIMINARY: Data Sheets contain information regarding a product M/A-COM Technology Solutions has under development. Performance is based on engineering tests. Specifications are typical. Mechanical outline has been fixed. Engineering samples and/or test data may be exailable. Commitment to produce in volume is not quaranteed.

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